

BAT54-A-C-S SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25^\circ\text{C}$)

Forward Current

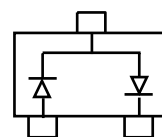
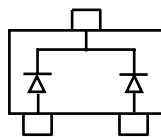
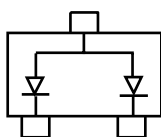
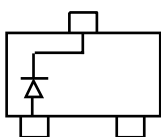
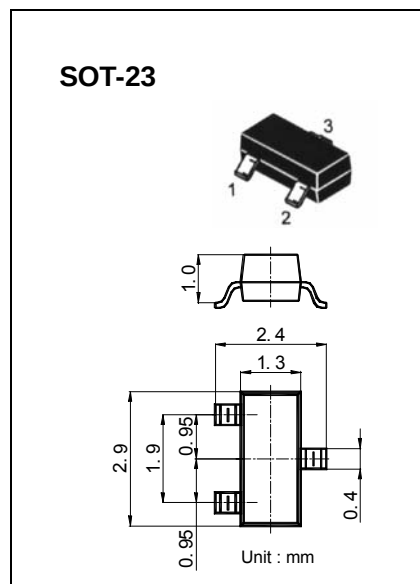
I_F : 200 mA

Reverse Voltage

V_R : 30 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$



BAT54 Marking: KL1

BAT54A Marking: KL2

BAT54C Marking: KL3

BAT54S Marking: KL4

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30		V
Reverse voltage leakage current	I_R	$V_R=25\text{V}$		2	μA
Forward voltage	V_F	$I_F=0.1\text{mA}$ $I_F=1\text{mA}$ $I_F=10\text{mA}$ $I_F=30\text{mA}$ $I_F=100\text{mA}$		240 320 400 500 1000	mV
Diode capacitance	C_D	$V_R=1\text{V}, f=1\text{MHz}$		10	pF
Reverse recovery time	t_{rr}	$I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1.0\text{mA}$ $R_C=100\Omega$		5	nS